

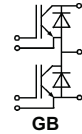
Absolute Maximum Ratings		Values	Units
Symbol	Conditions <sup>1)</sup>		
V <sub>CES</sub>		600	V
V <sub>CGR</sub>	R <sub>GE</sub> = 20 kΩ	600	V
I <sub>C</sub>	T <sub>case</sub> = 25/70 °C	260 / 200	A
I <sub>CM</sub>	T <sub>case</sub> = 25/70 °C; t <sub>p</sub> = 1 ms	450 / 400	A
V <sub>GES</sub>		± 20	V
P <sub>tot</sub>	per IGBT, T <sub>case</sub> = 25 °C	875	W
T <sub>j</sub> ; (T <sub>stg</sub> )		-40 ... +150 (125)	°C
V <sub>isol</sub>	AC, 1 min.	2 500	V
humidity	DIN 40 040	Class F	
climate	DIN IEC 68 T.1	40/125/56	
<b>Inverse Diode</b>			
I <sub>F</sub> = -I <sub>C</sub>	T <sub>case</sub> = 25/80 °C	200 / 135	A
I <sub>FM</sub> = -I <sub>CM</sub>	T <sub>case</sub> = 25/80 °C; t <sub>p</sub> = 1 ms	450 / 400	A
I <sub>FSM</sub>	t <sub>p</sub> = 10 ms; sin.; T <sub>j</sub> = 150 °C	1 400	A
I <sup>2</sup> t	t <sub>p</sub> = 10 ms; T <sub>j</sub> = 150 °C	9 800	A <sup>2</sup> s

**SEMİTRANS® M Superfast NPT-IGBT Modules**

**SKM 200 GB 063 D**



**SEMİTRANS 3**



- Features**
- N channel, homogeneous Silicon structure (NPT- Non punch-through IGBT)
  - Low tail current with low temperature dependence
  - High short circuit capability, self limiting if term. G is clamped to E
  - Pos. temp.-coeff. of V<sub>CEsat</sub>
  - 50 % less turn off losses <sup>9)</sup>
  - 30 % less short circuit current <sup>9)</sup>
  - Very low C<sub>ies</sub>, C<sub>oes</sub>, C<sub>res</sub> <sup>9)</sup>
  - Latch-up free
  - Fast & soft inverse CAL diodes <sup>8)</sup>
  - Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
  - Large clearance (13 mm) and creepage distances (20 mm)
- Typical Applications**
- Switching (not for linear use)
  - Switched mode power supplies
  - AC inverter servo drives
  - UPS uninterruptable power supplies
  - Welding inverters

<sup>1)</sup> T<sub>case</sub> = 25 °C, unless otherwise specified  
<sup>2)</sup> I<sub>F</sub> = -I<sub>C</sub>, V<sub>R</sub> = 300 V, -di<sub>F</sub>/dt = 1500 A/μs, V<sub>GE</sub> = 0 V  
<sup>3)</sup> Use V<sub>GEoff</sub> = -5 ... -15 V  
<sup>8)</sup> CAL = Controlled Axial Lifetime Technology  
<sup>9)</sup> Compared to PT-IGBT

Cases and mech. data → B 6 – 50

Characteristics		min.	typ.	max.	Units
Symbol	Conditions <sup>1)</sup>				
V <sub>(BR)CES</sub>	V <sub>GE</sub> = 0, I <sub>C</sub> = 4 mA	≥ V <sub>CES</sub>	-	-	V
V <sub>GE(th)</sub>	V <sub>GE</sub> = V <sub>CE</sub> , I <sub>C</sub> = 4 mA	4,5	5,5	6,5	V
I <sub>CES</sub>	V <sub>GE</sub> = 0, T <sub>j</sub> = 25 °C	-	2	6	mA
I <sub>GES</sub>	V <sub>CE</sub> = V <sub>CES</sub> , T <sub>j</sub> = 125 °C	-	12	-	mA
I <sub>GESat</sub>	V <sub>GE</sub> = 20 V, V <sub>CE</sub> = 0	-	-	1	μA
V <sub>CEsat</sub>	I <sub>C</sub> = 150 A, V <sub>GE</sub> = 15 V;	-	1,8(2,0)	-	V
V <sub>CEsat</sub>	I <sub>C</sub> = 200 A, T <sub>j</sub> = 25 (125) °C	-	2,1(2,4)	2,5(2,8)	V
g <sub>fs</sub>	V <sub>CE</sub> = 20 V, I <sub>C</sub> = 200 A	60	-	-	S
C <sub>CHC</sub>	per IGBT	-	-	700	pF
C <sub>ies</sub>	V <sub>GE</sub> = 0	-	11,2	-	nF
C <sub>oes</sub>	V <sub>CE</sub> = 25 V	-	1250	-	pF
C <sub>res</sub>	f = 1 MHz	-	750	-	pF
L <sub>CE</sub>		-	-	20	nH
t <sub>d(on)</sub>	V <sub>CC</sub> = 300 V	-	140	-	ns
t <sub>r</sub>	V <sub>GE</sub> = -15 V / +15 V <sup>3)</sup>	-	70	-	ns
t <sub>d(off)</sub>	I <sub>C</sub> = 200 A, ind. load	-	442	-	ns
t <sub>f</sub>	R <sub>Gon</sub> = R <sub>Goff</sub> = 8 Ω	-	45	-	ns
E <sub>on</sub>	T <sub>j</sub> = 125 °C	-	11	-	mWs
E <sub>off</sub>		-	7,5	-	mWs
<b>Inverse Diode <sup>8)</sup></b>					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 150 A { V <sub>GE</sub> = 0 V;	-	1,45(1,35)	1,7	V
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 200 A { T <sub>j</sub> = 25 (125) °C }	-	1,55(1,55)	1,9	V
V <sub>TO</sub>	T <sub>j</sub> = 125 °C	-	-	0,9	V
r <sub>f</sub>	T <sub>j</sub> = 125 °C	-	4	5,5	mΩ
I <sub>RRM</sub>	I <sub>F</sub> = 200 A; T <sub>j</sub> = 125 °C <sup>2)</sup>	-	75	-	A
Q <sub>rr</sub>	I <sub>F</sub> = 200 A; T <sub>j</sub> = 125 °C <sup>2)</sup>	-	12,7	-	μC
<b>Thermal characteristics</b>					
R <sub>thjc</sub>	per IGBT	-	-	0,14	°C/W
R <sub>thjc</sub>	per diode	-	-	0,3	°C/W
R <sub>thch</sub>	per module	-	-	0,038	°C/W

**SKM 200 GB 063 D**

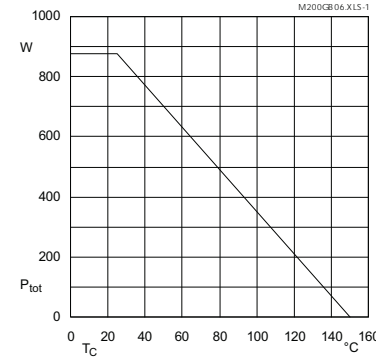


Fig. 1 Rated power dissipation P<sub>tot</sub> = f(T<sub>C</sub>)

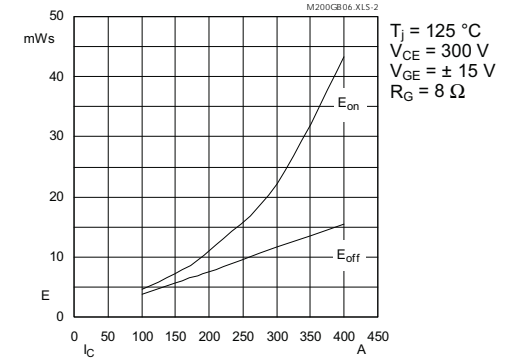


Fig. 2 Turn-on /-off energy = f(I<sub>C</sub>)

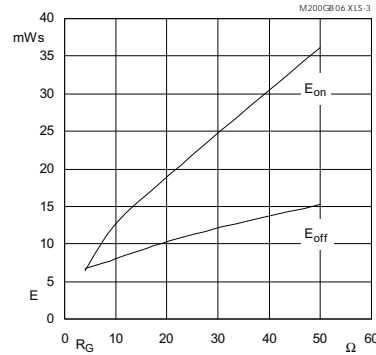


Fig. 3 Turn-on /-off energy = f(R<sub>G</sub>)

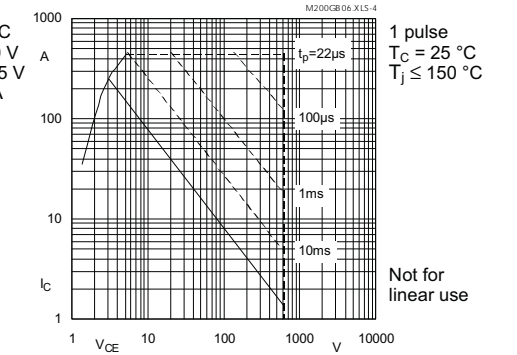


Fig. 4 Maximum safe operating area (SOA) I<sub>C</sub> = f(V<sub>CE</sub>)

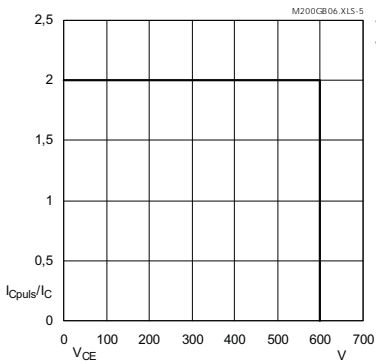


Fig. 5 Turn-off safe operating area (RBSOA)

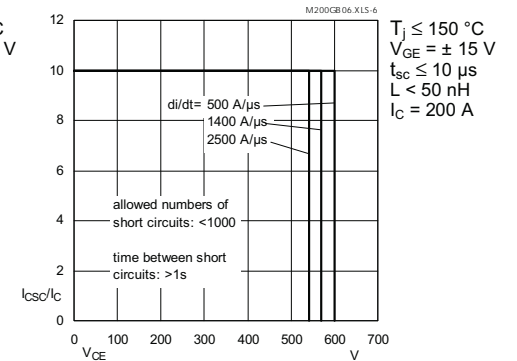


Fig. 6 Safe operating area at short circuit I<sub>C</sub> = f(V<sub>CE</sub>)

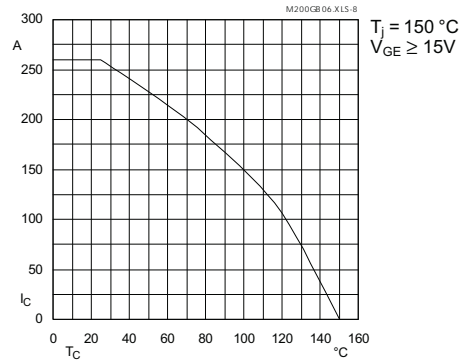


Fig. 8 Rated current vs. temperature  $I_C = f(T_C)$

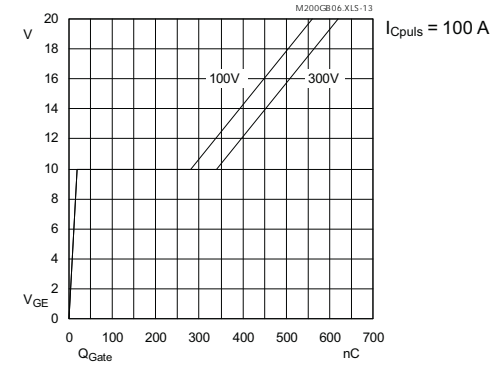


Fig. 13 Typ. gate charge characteristic

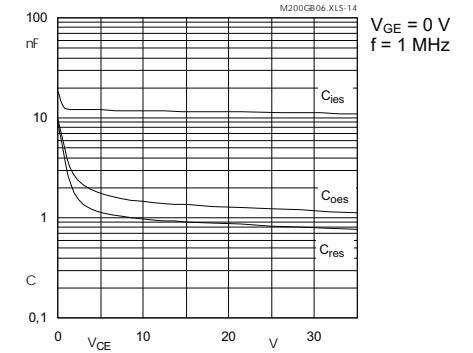


Fig. 14 Typ. capacitances vs.  $V_{CE}$

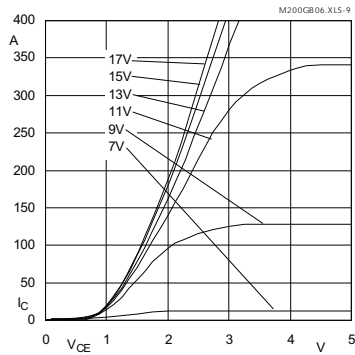


Fig. 9 Typ. output characteristic,  $t_p = 250 \mu s$ ;  $T_J = 25 \text{ }^\circ\text{C}$

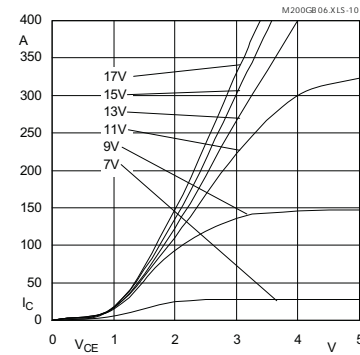


Fig. 10 Typ. output characteristic,  $t_p = 250 \mu s$ ;  $T_J = 125 \text{ }^\circ\text{C}$

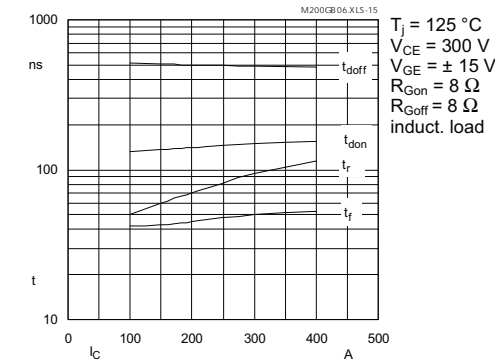


Fig. 15 Typ. switching times vs.  $I_C$

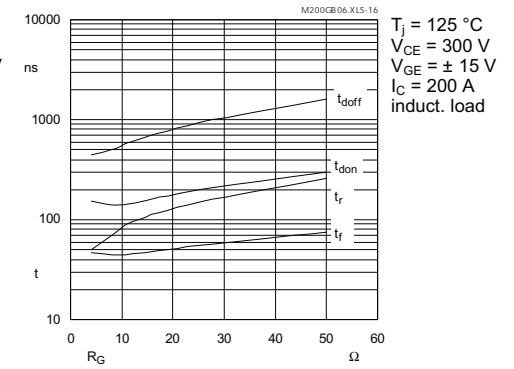


Fig. 16 Typ. switching times vs. gate resistor  $R_G$

$$P_{cond(t)} = V_{CEsat(t)} \cdot I_C(t)$$

$$V_{CEsat(t)} = V_{CE(TO)(T_J)} + r_{CE(T_J)} \cdot I_C(t)$$

$$V_{CE(TO)(T_J)} \leq 1,2 - 0,001 (T_J - 25) [V]$$

$$\text{typ.: } r_{CE(T_J)} = 0,0045 + 0,00002 (T_J - 25) [\Omega]$$

$$\text{max.: } r_{CE(T_J)} = 0,0065 + 0,00002 (T_J - 25) [\Omega]$$

$$\text{valid for } V_{GE} = + 15 \frac{+2}{-1} [V]; I_C \geq 0,3 I_{Cn}$$

Fig. 11 Saturation characteristic (IGBT)  
Calculation elements and equations

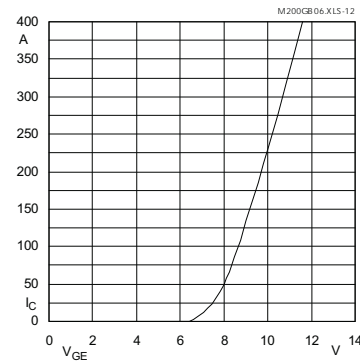


Fig. 12 Typ. transfer characteristic,  $t_p = 250 \mu s$ ;  $V_{CE} = 20 \text{ V}$

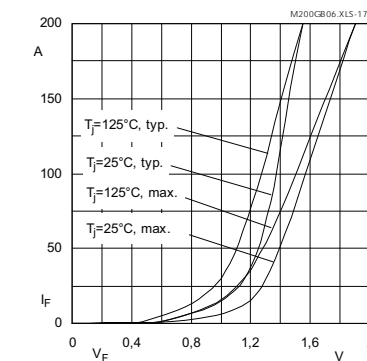


Fig. 17 Typ. CAL diode forward characteristic

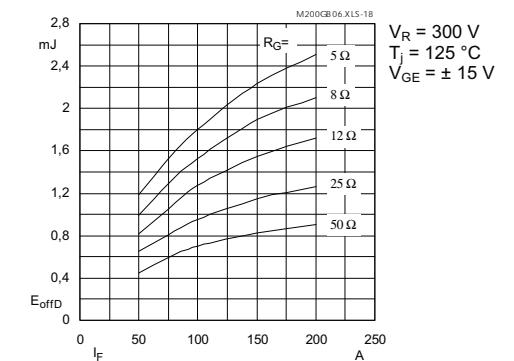


Fig. 18 Diode turn-off energy dissipation per pulse

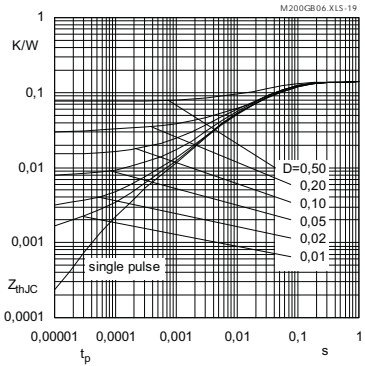


Fig. 19 Transient thermal impedance of IGBT  
 $Z_{thJC} = f(t_p)$ ;  $D = t_p / t_c = t_p \cdot f$

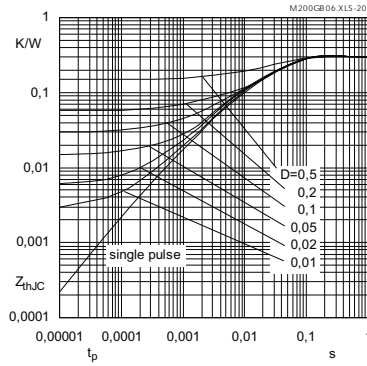


Fig. 20 Transient thermal impedance of inverse CAL diodes  
 $Z_{thJC} = f(t_p)$ ;  $D = t_p / t_c = t_p \cdot f$

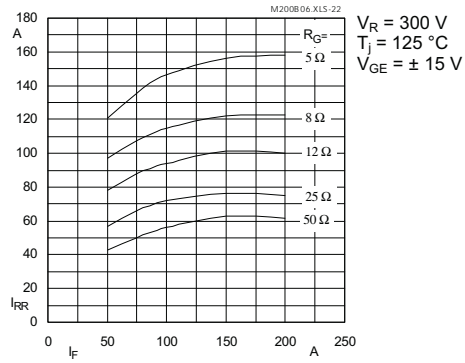


Fig. 22 Typ. CAL diode peak reverse recovery current  $I_{RR} = f(I_F; R_G)$

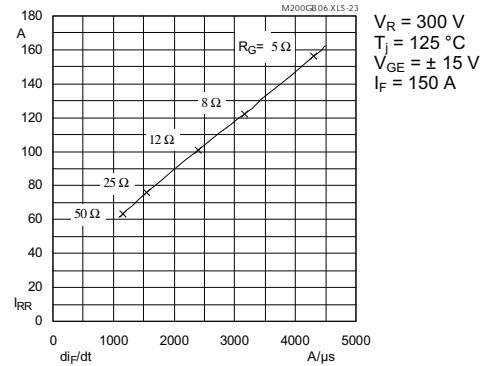


Fig. 23 Typ. CAL diode peak reverse recovery current  $I_{RR} = f(di/dt)$

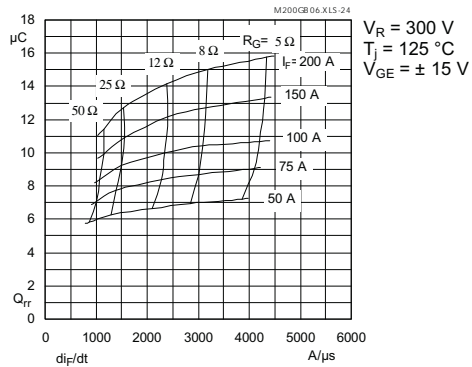
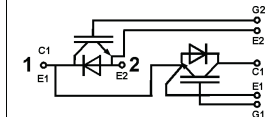
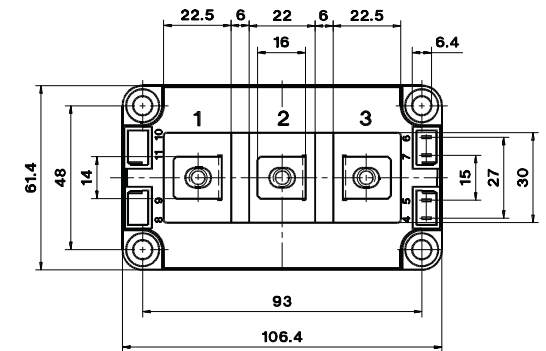
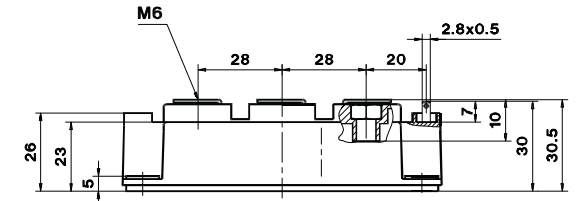


Fig. 24 Typ. CAL diode recovered charge

## SKM 200 GB 063 D

**SEMITRANS 3**  
 Case D 56  
 UL Recognized  
 File no. E 63 532

CASED56



Dimensions in mm

Case outline and circuit diagram

Mechanical Data		Values			Units
Symbol	Conditions	min.	typ.	max.	
M <sub>1</sub>	to heatsink, SI Units(M6) to heatsink, US Units	3	—	5	Nm lb.in.
M <sub>2</sub>	for terminals, SI Units(M6) for terminals, US Units	2,5	—	4	Nm lb.in.
a		—	—	5x9,81	m/s <sup>2</sup>
w		—	—	325	g

This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.

Eight devices are supplied in one SEMIBOX A without mounting hardware, which can be ordered separately under Ident No. 33321100 (for 10 SEMITRANS 3). Larger packing units of 12 or 20 pieces are used if suitable Accessories → B 6 – 4 SEMIBOX → C - 1.